# Sensitive Gate Silicon Controlled Rectifiers Reverse Blocking Thyristors

Annular PNPN devices designed for high volume consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-92/TO-226AA package which is readily adaptable for use in automatic insertion equipment.

#### Features

- Sensitive Gate Trigger Current 200 μA Maximum
- Low Reverse and Forward Blocking Current 50  $\mu A$  Maximum,  $T_C$  = 110°C
- Low Holding Current 5 mA Maximum
- Passivated Surface for Reliability and Uniformity
- These are Pb-Free Devices

MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
$\begin{tabular}{lll} Peak Repetitive Off-State Voltage (Note 1) \\ (T_J = -40 to 110 ^{\circ}C, Sine Wave, \\ 50 to 60 Hz, R_{GK} = 1 k \Omega) & 2N5060 \\ 2N5061 & 2N5062 \\ 2N5064 & 2N5064 \\ \end{tabular}$	V <sub>DRM</sub> , V <sub>RRM</sub>	30 60 100 200	V
On-State Current RMS (180° Conduction Angles; T <sub>C</sub> = 80°C)	I <sub>T(RMS)</sub>	0.8	Α
*Average On-State Current (180° Conduction Angles) $ (T_C = 67^\circ C) $ $ (T_C = 102^\circ C) $	I <sub>T(AV)</sub>	0.51 0.255	А
*Peak Non-repetitive Surge Current, T <sub>A</sub> = 25°C (1/2 cycle, Sine Wave, 60 Hz)	I <sub>TSM</sub>	10	Α
Circuit Fusing Considerations (t = 8.3 ms)	l <sup>2</sup> t	0.4	A <sup>2</sup> s
*Average On-State Current (180° Conduction Angles) $(T_C = 67^{\circ}C)$ $(T_C = 102^{\circ}C)$	I <sub>T(AV)</sub>	0.51 0.255	А
*Forward Peak Gate Power (Pulse Width $\leq$ 1.0 $\mu$ sec; $T_A = 25^{\circ}C$ )	P <sub>GM</sub>	0.1	W
*Forward Average Gate Power (T <sub>A</sub> = 25°C, t = 8.3 ms)	P <sub>G(AV)</sub>	0.01	W
*Forward Peak Gate Current (Pulse Width ≤ 1.0 μsec; T <sub>A</sub> = 25°C)	I <sub>GM</sub>	1.0	Α
*Reverse Peak Gate Voltage (Pulse Width ≤ 1.0 μsec; T <sub>A</sub> = 25°C)	V <sub>RGM</sub>	5.0	V
*Operating Junction Temperature Range	TJ	-40 to +110	°C
*Storage Temperature Range	T <sub>stg</sub>	–40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

\*Indicates JEDEC Registered Data.

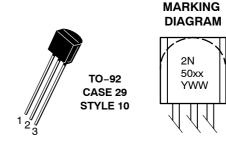


ON Semiconductor®

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# SILICON CONTROLLED RECTIFIERS 0.8 A RMS, 30 – 200 V





50xx Specific Device Code Y = Year WW = Work Week

PIN ASSIGNMENT			
1 Cathode			
2	Gate		
3	Anode		

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Thermal Resistance, Junction-to-Case (Note 2)	$R_{ heta JC}$	75	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W

<sup>2.</sup> This measurement is made with the case mounted "flat side down" on a heatsink and held in position by means of a metal clamp over the curved surface.

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•		•	•	•
*Peak Repetitive Forward or Reverse Blocking Curro (V <sub>AK</sub> = Rated V <sub>DRM</sub> or V <sub>RRM</sub> )	ent (Note 3) T <sub>C</sub> = 25°C T <sub>C</sub> = 110°C	I <sub>DRM</sub> , I <sub>RRM</sub>	- -	- -	10 50	μ <b>Α</b> μ <b>Α</b>
ON CHARACTERISTICS						
*Peak Forward On-State Voltage (Note 4) (I <sub>TM</sub> = 1.2 A peak @ T <sub>A</sub> = 25°C)		$V_{TM}$	-	-	1.7	V
Gate Trigger Current (Continuous DC) (Note 5) $*(V_{AK} = 7.0 \text{ Vdc}, R_L = 100 \Omega)$	T <sub>C</sub> = 25°C T <sub>C</sub> = -40°C	I <sub>GT</sub>	- -	- -	200 350	μΑ
Gate Trigger Voltage (Continuous DC) (Note 5) $*(V_{AK} = 7.0 \text{ Vdc}, R_L = 100 \Omega)$	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	V <sub>GT</sub>	-	- -	0.8 1.2	V
*Gate Non-Trigger Voltage $(V_{AK} = Rated \ V_{DRM}, \ R_L = 100 \ \Omega) \ T_C = 110^{\circ}C$		V <sub>GD</sub>	0.1	-	-	V
Holding Current (Note 3) *(V <sub>AK</sub> = 7.0 Vdc, initiating current = 20 mA)	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	lн	- -	- -	5.0 10	mA
Turn-On Time Delay Time Rise Time $(I_{GT} = 1.0 \text{ mA}, V_D = \text{Rated } V_{DRM},$ Forward Current = 1.0 A, di/dt = 6.0 A/ $\mu$ s		t <sub>d</sub> t <sub>r</sub>	-	3.0 0.2	- -	μs
Turn-Off Time (Forward Current = 1.0 A pulse, Pulse Width = 50 $\mu$ s, 0.1% Duty Cycle, di/dt = 6.0 A/ $\mu$ s, dv/dt = 20 V/ $\mu$ s, I <sub>GT</sub> = 1 mA) 2N5060, 2	2N5061	tq	_	10	_	μS
2N5062, 2	2N5064		-	30	_	
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off–State Voltage (Rated $V_{DRM}$ , Exponential, $R_{GK} = 1 \text{ k}\Omega$ )		dv/dt		30		V/µs

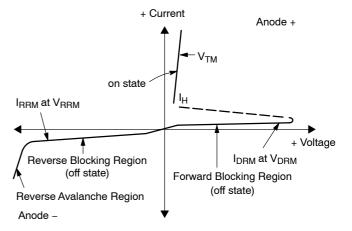
<sup>\*</sup>Indicates JEDEC Registered Data.

<sup>\*</sup>Indicates JEDEC Registered Data.

<sup>3.</sup>  $R_{GK}$  = 1000  $\Omega$  is included in measurement. 4. Forward current applied for 1 ms maximum duration, duty cycle  $\leq$  1%. 5.  $R_{GK}$  current is not included in measurement.

## **Voltage Current Characteristic of SCR**

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Off State Forward Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Off State Reverse Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Peak on State Voltage
I <sub>H</sub>	Holding Current



#### **CURRENT DERATING**

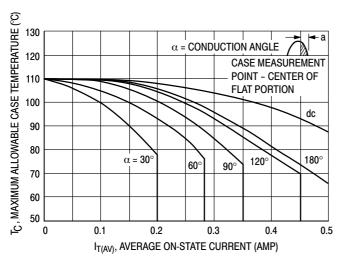


Figure 1. Maximum Case Temperature

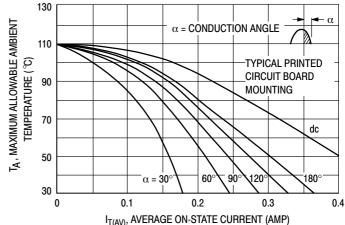


Figure 2. Maximum Ambient Temperature

## **CURRENT DERATING**

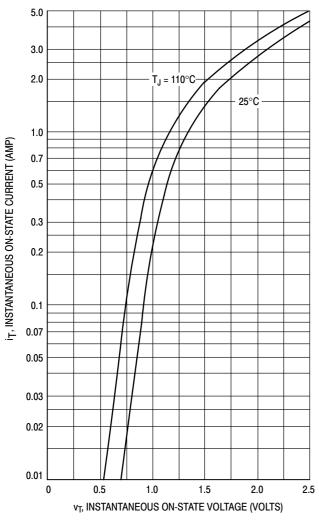


Figure 3. Typical Forward Voltage

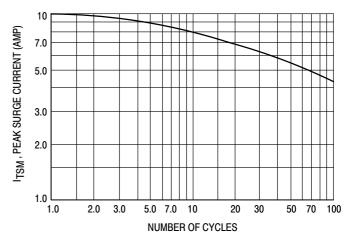


Figure 4. Maximum Non-Repetitive Surge Current

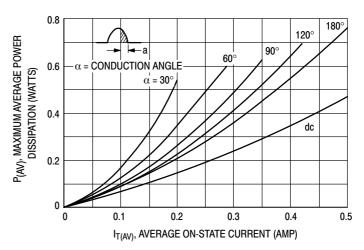


Figure 5. Power Dissipation

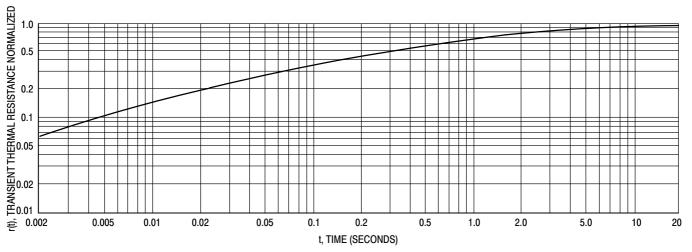
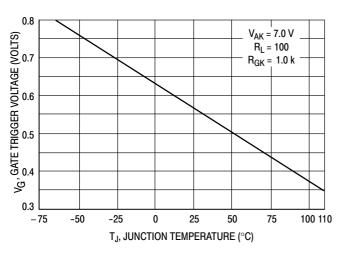


Figure 6. Thermal Response

## **TYPICAL CHARACTERISTICS**



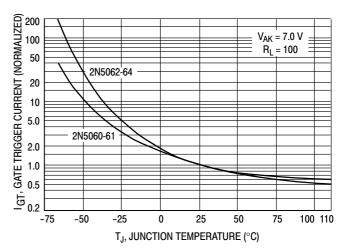


Figure 7. Typical Gate Trigger Voltage

Figure 8. Typical Gate Trigger Current

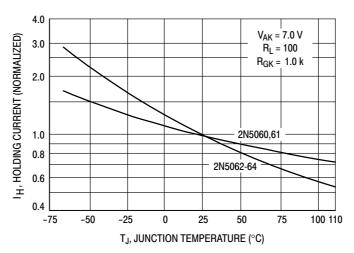


Figure 9. Typical Holding Current

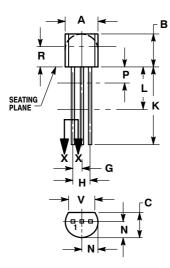
## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
2N5060G	TO-92 (Pb-Free)	5000 Units / Box
2N5060RLRA	TO-92	2000 / Tape & Reel
2N5060RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N5060RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N5061G	TO-92 (Pb-Free)	5000 Units / Box
2N5061RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N5062G	TO-92 (Pb-Free)	5000 Units / Box
2N5062RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N5064RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N5064RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N5064G	TO-92 (Pb-Free)	5000 Units / Box

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

#### TO-92 (TO-226) CASE 29-11 **ISSUE AM**



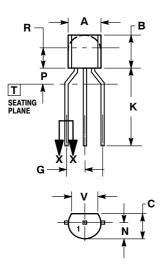
STRAIGHT LEAD **BULK PACK** 



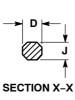
#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
_	0.015	0.020	0.39	0.50
K	0.500		12.70	
٦	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



**BENT LEAD** TAPF & RFFI AMMO PACK



#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
C	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
Р	1.50	4.00	
R	2.93		
٧	3.43		

#### STYLE 10: PIN 1. CATHODE

- GATE
- 3. ANODE

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